

ABSTRACT

The present application relates to the technical field of semiconductor manufacturing, in particular to a method for processing a semiconductor structure. The method for processing a semiconductor structure comprises the following steps: providing a semiconductor structure, the semiconductor structure comprising a substrate and a plurality of etching structures located on a surface region of the substrate; forming a transition layer at least covering an inner wall of each etching structure, with the transition layer being used for reducing the capillary force of a fluid on the etching structures and serving as a sacrificial layer for repairing a collapsed structure; drying the semiconductor structure; and removing the transition layer. The present application reduces the probability of collapse or deformation of an etching structure in a cleaning process, improves the performance of a semiconductor structure, and improves the productive rate and the yield of a semiconductor device.

Fig. 1